

8-Channel Fault-Protected Analog Multiplexer

ADG528F

FEATURES

Low on resistance (300 Ω typical) Fast switching times toN: 250 ns maximum toFF: 250 ns maximum Low power dissipation (3.3 mW maximum) Fault and overvoltage protection (-40 V to +55 V) All switches off with power supply off Analog output of on channel clamped within power supplies if an overvoltage occurs Latch-up proof construction Break-before-make construction TTL and CMOS compatible inputs

APPLICATIONS

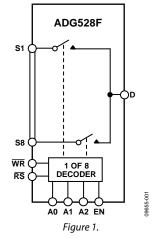
Existing multiplexer applications (both fault-protected and nonfault-protected) New designs requiring multiplexer functions

GENERAL DESCRIPTION

The ADG528F¹ is a CMOS analog multiplexer, with the comprising eight single channels. This multiplexer provides fault protection. Using a series n-channel, p-channel, n-channel MOSFET structure, both device and signal source protection is provided in the event of an overvoltage or power loss. The multiplexer can withstand continuous overvoltage inputs from -40 V to +55 V. During fault conditions, the multiplexer input (or output) appears as an open circuit and only a few nanoamperes of leakage current will flow. This protects not only the multiplexer and the circuitry driven by the multiplexer, but also protects the sensors or signal sources that drive the multiplexer.

The ADG528F switches one of eight inputs to a common output as determined by the 3-bit binary address lines A0, A1, and A2. The ADG528F has on-chip address and control latches that facilitate microprocessor interfacing. An EN input on the device is used to enable or disable the device. When disabled, all channels are switched off.

FUNCTIONAL BLOCK DIAGRAM



PRODUCT HIGHLIGHTS

1. Fault protection.

The ADG528F can withstand continuous voltage inputs from -40 V to +55 V. When a fault occurs due to the power supplies being turned off, all the channels are turned off and only a leakage current of a few nanoamperes flows.

- 2. On channel turns off while fault exists.
- 3. Low Ron.
- 4. Fast switching times.
- Break-before-make switching. Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
- Trench isolation eliminates latch-up. A dielectric trench separates the p-channel and n-channel MOSFETs thereby preventing latch-up.

Rev. F

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ADG528F* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

View a parametric search of comparable parts.

DOCUMENTATION

Application Notes

- AN-1024: How to Calculate the Settling Time and Sampling Rate of a Multiplexer
- AN-32: Single Supply Operation of JFET Multiplexers

Data Sheet

 ADG528F: 8-Channel Fault-Protected Analog Multiplexer Data Sheet

TOOLS AND SIMULATIONS \square

ADG528F SPICE Macro-Model

REFERENCE MATERIALS

Product Selection Guide

• Switches and Multiplexers Product Selection Guide

Technical Articles

- CMOS Switches Offer High Performance in Low Power, Wideband Applications
- Data-acquisition system uses fault protection
- Enhanced Multiplexing for MEMS Optical Cross Connects
- Temperature monitor measures three thermal zones

DESIGN RESOURCES

- ADG528F Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all ADG528F EngineerZone Discussions.

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REVISION HISTORY

7/11-Rev. E to Rev. F

Deleted ADG508F/ADG509F	Universal
Changes to Table 3	6
Added Table 4	7
Updated Outline Dimensions	
Changes to Ordering Guide	

7/09—Rev. D to Rev. E

Updated Format	Universal
Added TSSOP	Universal
Updated Outline Dimensions	15
Changes to Ordering Guide	

4/01—Data Sheet Changed from Rev. C to Rev. D.

Changes to Ordering Guide	1
Changes to Specifications Table	2
Max Ratings Changed	4
Deleted 16-Lead Cerdip from Outline Dimensions	. 11
Deleted 18-Lead Cerdip from Outline Dimensions	. 12

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SPECIFICATIONS

DUAL SUPPLY

 V_{DD} = +15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

		B Version		
Parameter	+25°C	–40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		V _{SS} + 3	V min	
		V _{DD} – 1.5	V max	
Ron	300	350	Ωtyp	$-10 V \le V_S \le +10 V$, $I_S = 1 mA$;
				V_{DD} = +15 V ± 10%, V_{SS} = -15 V ± 10%
		400	Ωmax	$-10 V \le V_S \le +10 V$, $I_S = 1 mA$;
				$V_{DD} = +15 V \pm 5\%$, $V_{SS} = -15 V \pm 5\%$
Ron Drift	0.6		%/°C typ	$V_{s} = 0 V, I_{s} = 1 mA$
R _{on} Match	5		% max	$V_{s} = 0 V, I_{s} = 1 mA$
LEAKAGE CURRENTS				
Source Off Leakage I _s (Off)	±0.02		nA typ	$V_D = \pm 10 \text{ V}, \text{ V}_S = \mp 10 \text{ V};$
	±1	±50	nA max	See Figure 19
Drain Off Leakage I _D (Off)	±0.04		nA typ	$V_D = \pm 10 V$, $V_S = \mp 10 V$;
	±1	±60	nA max	See Figure 20
Channel On Leakage I_D , I_S (On)	±0.04		nA typ	$V_{s} = V_{D} = \pm 10 V;$
	±1	±60	nA max	See Figure 21
FAULT				
Output Leakage Current	±0.02		nA typ	$V_s = \pm 33 \text{ V}, V_D = 0 \text{ V}$, see Figure 20
(With Overvoltage)	±2	±2	μA max	
Input Leakage Current	±0.005		μA typ	$V_s = \pm 25 V$, $V_D = \mp 10 V$, see Figure 22
(With Overvoltage)	±2		µA max	
Input Leakage Current	±0.001		μA typ	$V_{S} = \pm 25 V, V_{D} = V_{EN} = A0, A1, A2 = 0 V$
(With Power Supplies Off)	±2		µA max	See Figure 23
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, VINL		0.8	V max	
Input Current, Inl or Inh		±1	μA max	$V_{IN} = 0 \text{ or } V_{DD}$
C _{IN} , Digital Input Capacitance	5		pF typ	
DYNAMIC CHARACTERISTICS ¹				
t _{TRANSITION}	200		ns typ	$R_L = 1 M\Omega, C_L = 35 pF;$
	300	400	ns max	$V_{S1} = \pm 10 \text{ V}, V_{S8} = \mp 10 \text{ V}; \text{ see Figure 24}$
topen	50		ns typ	$R_L = 1 \text{ k}\Omega$, $C_L = 35 \text{ pF}$;
	25	10	ns min	$V_s = 5 V$; see Figure 25
ton (EN, WR)	200	-	ns typ	$R_L = 1 k\Omega$, $C_L = 35 pF$;
	250	400	ns max	$V_s = 5 V$; see Figure 26
t_{OFF} (EN, \overline{RS})	200		ns typ	$R_L = 1 k\Omega, C_L = 35 pF;$
t _{SETT} , Settling Time	250	400	ns max	$V_s = 5 V$; see Figure 26
0.1%	250	1	μs typ	$R_L = 1 k\Omega, C_L = 35 pF;$
0.01%		2.5	μs typ μs typ	$V_{\rm S} = 5 V$
tw, Write Pulse Width	100	120	ns min	v3-3 v
ts, Address, Enable Setup Time	100	100	ns min	
t _H , Address, Enable Hold Time		100	ns min	
t _{Rs} , Reset Pulse Width		100	ns min	
		100	112 111111	

		B Version			
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments	
Charge Injection	4		pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 29	
Off Isolation	68		dB typ	$R_L = 1 \text{ k}\Omega$, $C_L = 15 \text{ pF}$, $f = 100 \text{ kHz}$;	
	50		dB min	$V_s = 7 V rms$; see Figure 30	
Cs (Off)	5		pF typ		
C _D (Off)	50		pF typ		
POWER REQUIREMENTS					
ldd	0.1	0.2	mA max	$V_{IN} = 0 V \text{ or } 5 V$	
lss	0.1	0.1	mA max		

¹ Guaranteed by design, not subject to production test.

TRUTH TABLE

Table 2. ADG528F Truth Table¹

A2	A1	A0	EN	WR	RS	On Switch
Х	Х	Х	Х	▲	1	Retains previous switch condition
Х	Х	Х	Х	Х	0	None (address and enable latches cleared)
Х	Х	Х	0	0	1	None
0	0	0	1	0	1	1
0	0	1	1	0	1	2
0	1	0	1	0	1	3
0	1	1	1	0	1	4
1	0	0	1	0	1	5
1	0	1	1	0	1	6
1	1	0	1	0	1	7
1	1	1	1	0	1	8

 1 X = don't care.

TIMING DIAGRAMS

Figure 2 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while \overline{WR} is held low, the latches are transparent and the switches respond to the address and enable inputs.

This input data is latched on the rising edge of \overline{WR} . Figure 3 shows the reset pulse width, t_{RS} , and the reset turnoff time, t_{OFF} (\overline{RS}). Note that all digital input signals rise and fall times are measured from 10% to 90% of 3 V. $t_R = t_F = 20$ ns.

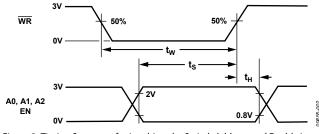
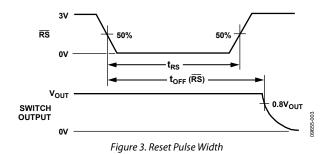


Figure 2. Timing Sequence for Latching the Switch Address and Enable Inputs



ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$ unless otherwise noted.

Table 3.

Parameter	Rating
V _{DD} to V _{SS}	44 V
V _{DD} to GND	–0.3 V to +25 V
Vss to GND	+0.3 V to -25 V
Digital Input, EN, Ax	–0.3 V to V _{DD} + 2 V or 20 mA, whichever occurs first
V _s , Analog Input Overvoltage with Power On ($V_{DD} = +15 \text{ V}, \text{ V}_{ss} = -15 \text{ V}$)	$V_{\text{SS}}-25$ V to $V_{\text{DD}}+40$ V
V_s , Analog Input Overvoltage with Power Off ($V_{DD} = 0 V$, $V_{SS} = 0 V$)	–40 V to +55 V
Continuous Current, S or D	20 mA
Peak Current, S or D	
(Pulsed at 1 ms, 10% Duty Cycle Max)	40 mA
Operating Temperature Range	
Industrial (B Version)	–40°C to +85°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
θ _{JA} , Thermal Impedance	90°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

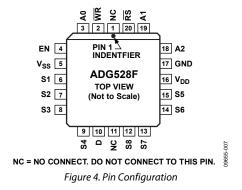


Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	NC	No Connect. This pin is open.
2	WR	Write. The \overline{WR} signal latches the state of the address control lines and the enable line.
3	AO	Logic Control Input.
4	EN	Active High Digital Input. When low, the device is disabled and all switches are off. When high, Ax logic inputs determine on switches.
5	V _{ss}	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.
6	S1	Source Terminal 1. This pin can be an input or an output.
7	S2	Source Terminal 2. This pin can be an input or an output.
8	S3	Source Terminal 3. This pin can be an input or an output.
9	S4	Source Terminal 4. This pin can be an input or an output.
10	D	Drain Terminal. This pin can be an input or an output.
11	NC	No Connect. This pin is open.
12	S8	Source Terminal 8. This pin can be an input or an output.
13	S7	Source Terminal 7. This pin can be an input or an output.
14	S6	Source Terminal 6. This pin can be an input or an output.
15	S5	Source Terminal 5. This pin can be an input or an output.
16	V _{DD}	Most Positive Power Supply Potential.
17	GND	Ground (0 V) Reference.
18	A2	Logic Control Input.
19	A1	Logic Control Input.
20	RS	Reset. The $\overline{\text{RS}}$ signal clears both the address and enable data in the latches resulting in no output (all switches off).

TYPICAL PERFORMANCE CHARACTERISTICS

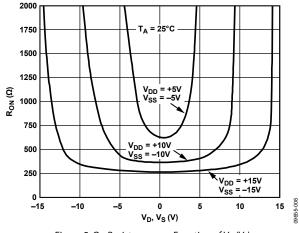


Figure 5. On Resistance as a Function of V_D (Vs)

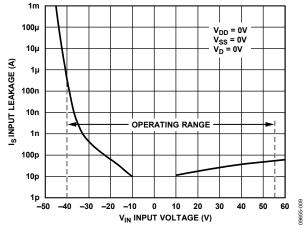


Figure 6. Input Leakage Current as a Function of V₅ (Power Supplies Off) During Overvoltage Conditions

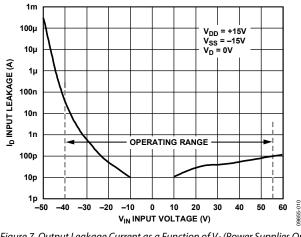


Figure 7. Output Leakage Current as a Function of V_S (Power Supplies On) During Overvoltage Conditions

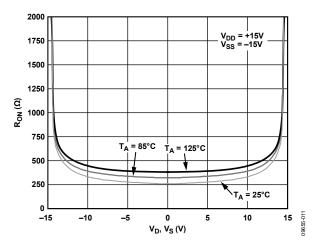


Figure 8. On Resistance as a Function of V_D (V_s) for Different Temperatures

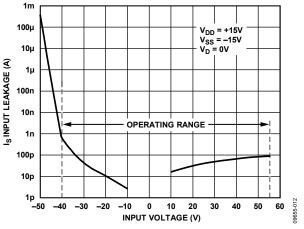
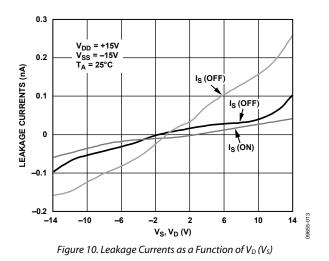


Figure 9. Input Leakage Current as a Function of V₅ (Power Supplies On) During Overvoltage Conditions



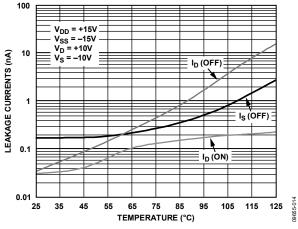


Figure 11. Leakage Currents as a Function of Temperature

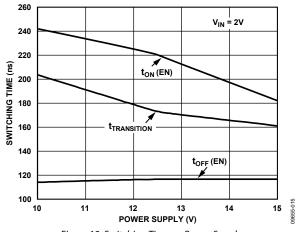
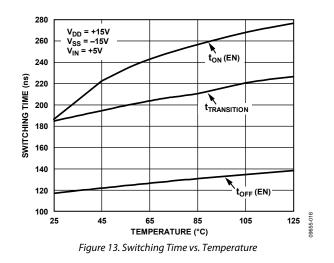


Figure 12. Switching Time vs. Power Supply



TERMINOLOGY

V_{DD} Most positive power supply potential.

 \mathbf{V}_{ss} Most negative power supply potential.

GND Ground (0 V) reference.

R_{ON} Ohmic resistance between D and S.

 \mathbf{R}_{ON} **Drift** Change in R_{ON} when temperature changes by one degree Celsius.

R_{ON} **Match** Difference between the R_{ON} of any two channels.

Is (Off) Source leakage current when the switch is off.

 $\mathbf{I}_{\mathrm{D}}\left(\mathbf{Off}\right)$ Drain leakage current when the switch is off.

 $I_{\rm D}, I_{\rm S}\left(On\right)$ Channel leakage current when the switch is on.

 $\mathbf{V}_{\mathrm{D}}\left(\mathbf{V}_{s}\right)$ Analog Voltage on Terminal D and Terminal S.

Cs (Off) Channel input capacitance for off condition.

 $\begin{array}{l} C_{D}\left(Off\right) \\ \mbox{Channel output capacitance for off condition.} \end{array}$

C_D, C_s (On) On switch capacitance.

Cin

Digital input capacitance.

 t_{ON} (EN) Delay time between the 50% and 90% points of the digital input and switch on condition.

 $t_{\mbox{\scriptsize OFF}}$ (EN) Delay time between the 50% and 90% points of the digital input and switch off condition.

tTRANSITION Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

topen Off time measured between 80% points of both switches when switching from one address state to another.

V_{INL}

Maximum input voltage for Logic 0.

 \mathbf{V}_{INH} Minimum input voltage for Logic 1.

I_{INL} (I_{INH}) Input current of the digital input.

Off Isolation

A measure of unwanted signal coupling through an off channel.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

I_{DD} Positive supply current.

Iss

Negative supply current.

THEORY OF OPERATION

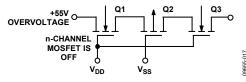
The ADG528F multiplexer is capable of withstanding overvoltages from -40 V to +55 V, irrespective of whether the power supplies are present or not. Each channel of the multiplexer consists of an n-channel MOSFET, a p-channel MOSFET, and an n-channel MOSFET, connected in series. When the analog input exceeds the power supplies, one of the MOSFETs will switch off, limiting the current to submicroamp levels, thereby preventing the overvoltage from damaging any circuitry following the multiplexer. Figure 14 illustrates the channel architecture that enables these multiplexers to withstand continuous overvoltages.

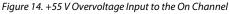
When an analog input of V_{SS} + 3 V to $V_{\rm DD}$ – 1.5 V is applied to the ADG528F, the multiplexer behaves as a standard multiplexer, with specifications similar to a standard multiplexer, for example, the on-resistance is 400 Ω maximum. However, when an overvoltage is applied to the device, one of the three MOSFETs will turn off.

Figure 14 to Figure 17 show the conditions of the three MOSFETs for the various overvoltage situations. When the analog input applied to an on channel approaches the positive power supply line, the n-channel MOSFET turns off because the voltage on the analog input exceeds the difference between V_{DD} and the n-channel threshold voltage (V_{TN}). When a voltage more negative than V_{SS} is applied to the multiplexer, the p-channel MOSFET will turn off because the analog input is more negative than the difference between V_{SS} and the p-channel threshold voltage (V_{TP}). Because V_{TN} is nominally 1.5 V and V_{TP} is typically 3 V, the analog input range to the multiplexer is limited to -12 V to +13.5 V when a ± 15 V power supply is used.

When the power supplies are present but the channel is off, again either the p-channel MOSFET or one of the n-channel MOSFETs will turn off when an overvoltage occurs.

Finally, when the power supplies are off, the gate of each MOSFET will be at ground. A negative overvoltage switches on the first n-channel MOSFET but the bias produced by the overvoltage causes the p-channel MOSFET to remain turned off. With a positive overvoltage, the first MOSFET in the series will remain off because the gate to source voltage applied to this MOSFET is negative. During fault conditions, the leakage current into and out of the ADG528F is limited to a few microamps. This protects the multiplexer and succeeding circuitry from over stresses as well as protecting the signal sources, which drive the multiplexer. Also, the other channels of the multiplexer will be undisturbed by the overvoltage and will continue to operate normally.





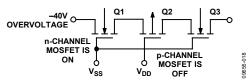


Figure 15. –40 V Overvoltage on an Off Channel with Multiplexer Power On

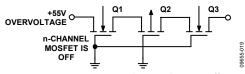


Figure 16. +55 V Overvoltage with Power Off

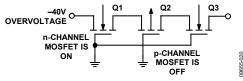
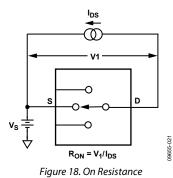
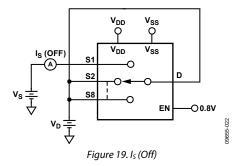
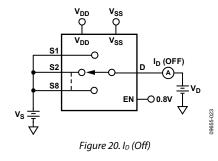


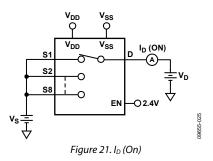
Figure 17. –40 V Overvoltage with Power Off

TEST CIRCUITS









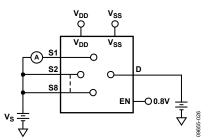


Figure 22. Input Leakage Current (with Overvoltage)

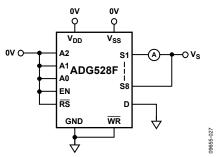


Figure 23. Input Leakage Current (with Power Supplies Off)

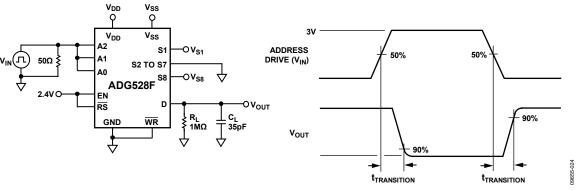


Figure 24. Switching Time of Multiplexer, transition

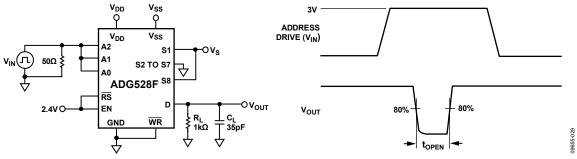
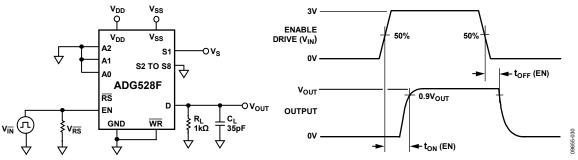
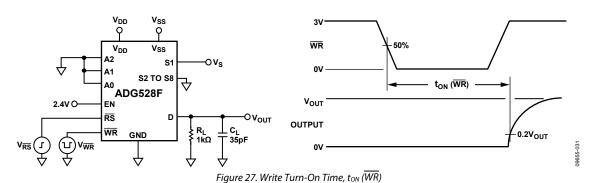
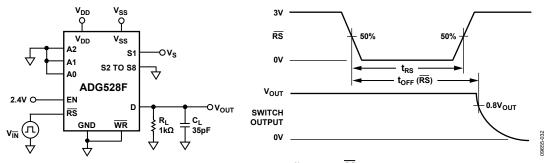


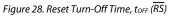
Figure 25. Break-Before-Make Delay, tOPEN











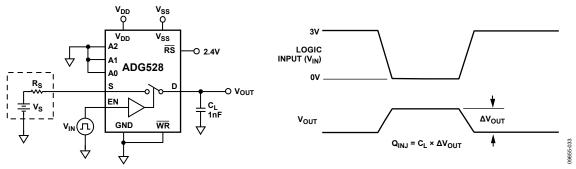
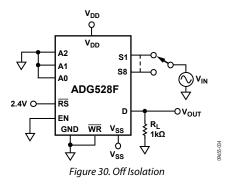
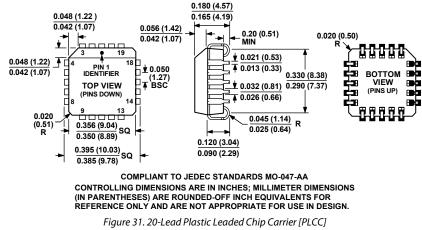


Figure 29. Charge Injection



OUTLINE DIMENSIONS



(P-20) Dimensions shown in inches and (millimeters)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADG528FBP	–40°C to +85°C	20-Lead PLCC	P-20
ADG528FBPZ	–40°C to +85°C	20-Lead PLCC	P-20

 1 Z = RoHS Compliant Part.

NOTES



www.analog.com

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